

Features

- Provides bias for GaAs and HEMT FETs
- Drives up to four FETs
- Dynamic FET protection
- Drain current set by external resistor
- Regulated negative rail generator requires only 2 external capacitors
- Choice in drain voltage
- Wide supply voltage range
- SSOP surface mount package

Applications

- Satellite receiver LNBS
- Private mobile radio (PMR)
- Cellular telephones

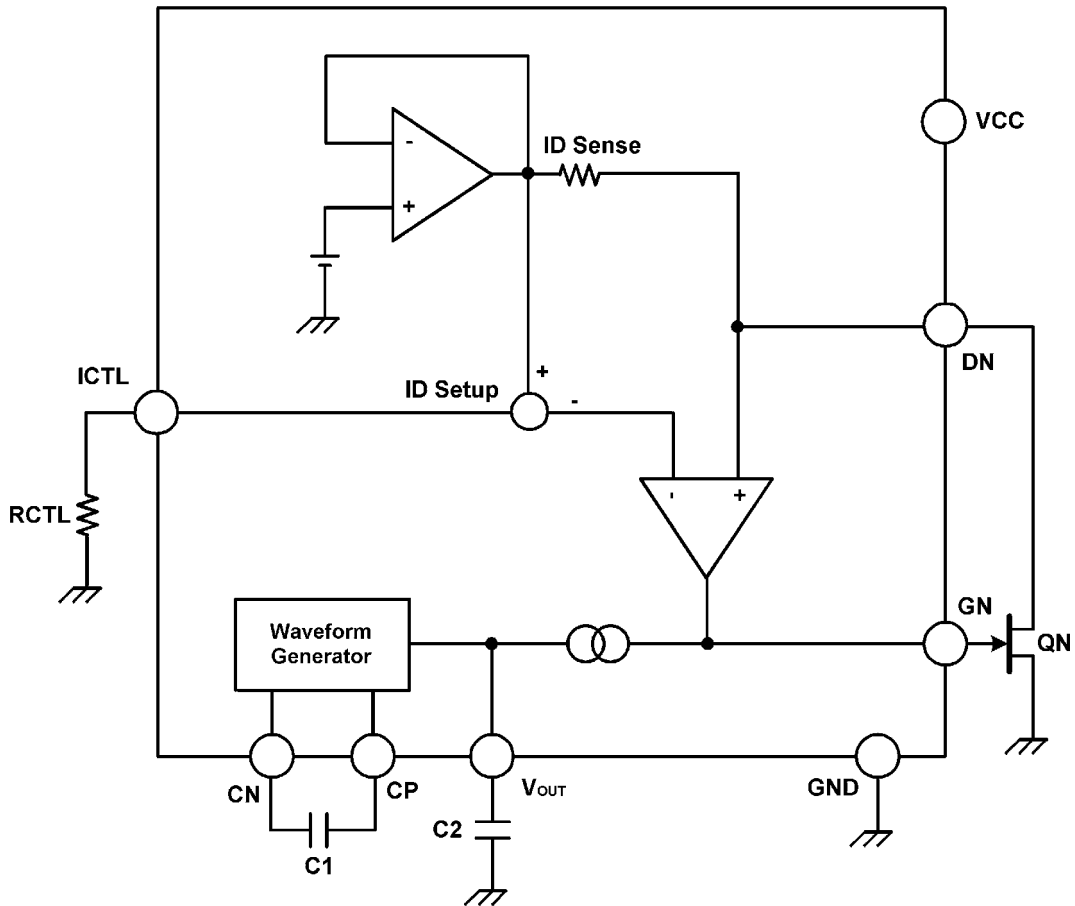
Block Diagram

Description

The AT1504 is designed to meet the bias requirements of GaAs and HEMT FETs commonly used in satellite receiver LNBS, PMR, cellular telephones etc. with a minimum of external components.

With the addition of two capacitors and resistors the devices provide drain voltage and current control for a number of external grounded source FETs.

The AT1504 is available in SSOP16 pin packages respectively for the minimum in devices size. Device operating temperature is -40 to 70°C to suit a wide range of environmental conditions.



Aimtron reserves the right without notice to change this circuitry and specifications.

Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	unit
Power supply voltage	V _{CC}	-0.6~15	V
Supply Current	I _{CC}	100	mA
Drain Current	V _D	0~15	mA
Operating temperature	T _{opr}	-40~+70	°C
Storage temperature	T _{stg}	-50~+85	°C
Power dissipation	P _d	500	mW

Recommended operating conditions (Ta = 25°C)

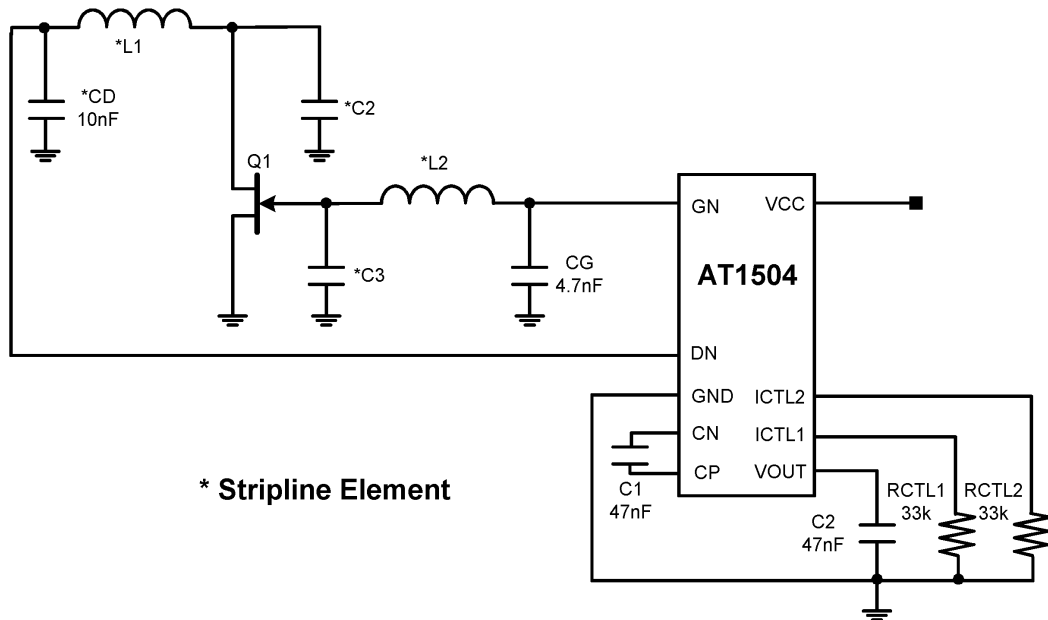
Parameter	Symbol	Limits	unit
Power supply voltage	V _{CC}	5~12	V

Electrical characteristics

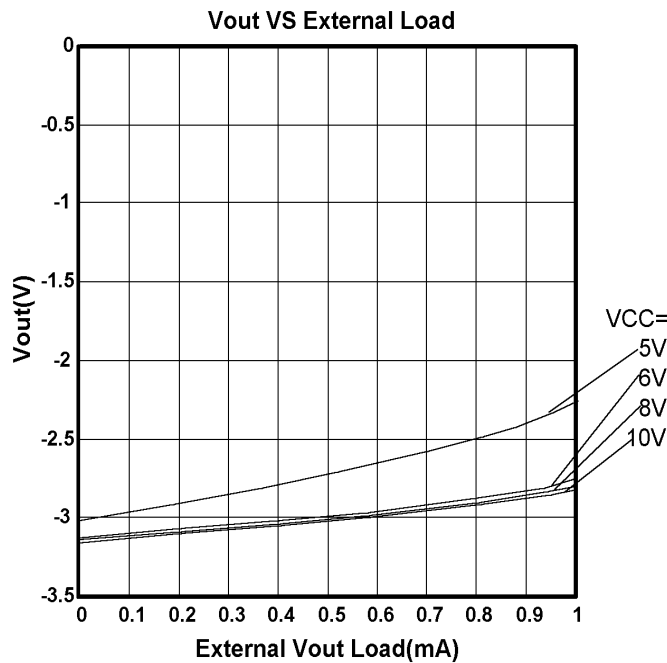
(Unless otherwise stated, Ta=25°C, V_{CC}=5V, I_D=10mA, R_{CTL1}=33kΩ, R_{CTL2}=33kΩ)

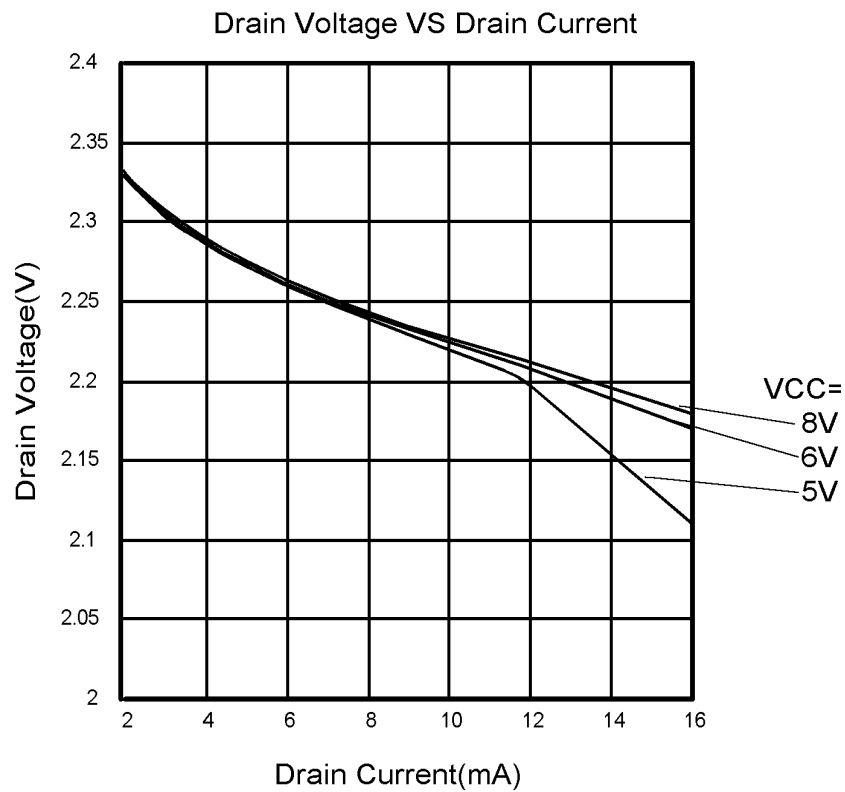
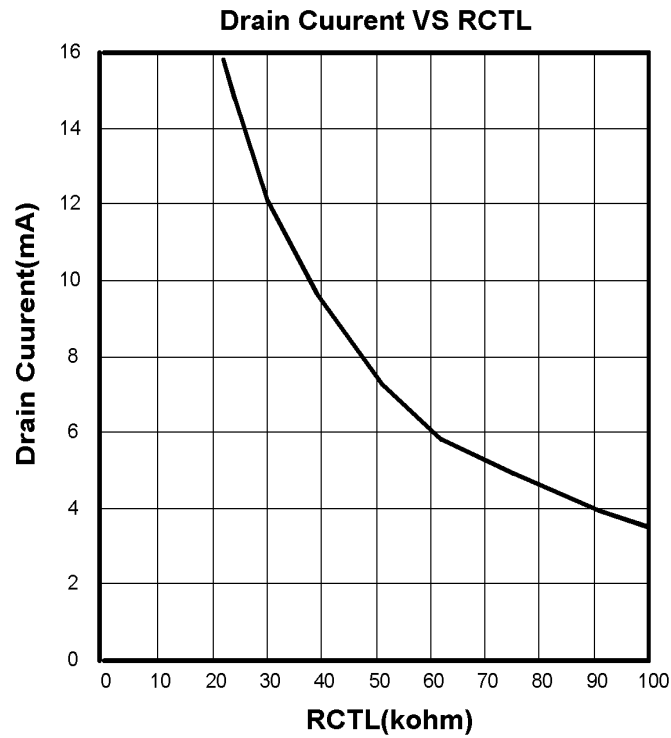
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Supply Voltage	V _{CC}	5	--	12	V	
Supply Current	I _{CC}	--	--	10	mA	I _{D1} to I _{D4} =0
		--	--	50	mA	I _{D1} to I _{D4} =10mA
Negative Voltage	V _{OUT}	-3.5	-3	-2	V	I _{OUT} = 0
		--	--	-2	V	I _{OUT} = -200μA
Drain Output Noise Voltage	E _{ND}	--	--	0.02	V _{PP}	C _G =4.7nF, C _D =10nF
Gate Output Noise Voltage	E _{NG}	--	--	0.005	V _{PP}	C _G =4.7nF, C _D =10nF
Oscillator Freq.	f _o	200	350	800	kHz	
DRAIN						
Drain Current	I _D	8	10	12	mA	
Drain Current Change with V _{CC}	ΔI _{DV}	--	0.02	--	%/V	V _{CC} =5 to 12V
Drain Current Change with T _j	ΔI _{DT}	--	0.05	--	%/°C	T _j =-40 to +70°C
Drain Voltage	V _D	2	2.2	2.4	V	
Drain Voltage Charge with V _{CC}	ΔV _{DV}	--	0.5	--	%/V	V _{CC} =5 to 12V
Drain Voltage Charge with T _j	ΔV _{DT}	--	50	--	ppm	T _j =-40 to +70°C
GATE						
Gate Output Current Range	I _{GO}	-30	--	2000	μA	
Gate Output Low Voltage	V _{OL}	-3.5	--	-2	V	I _{D1} to I _{D4} =12mA I _{G1} to I _{G4} =0
		-3.5	--	-2	V	I _{D1} to I _{D4} =12mA I _{G1} to I _{G4} = -10μA
Gate Output High Voltage	V _{OH}	0	--	1	V	I _{D1} to I _{D4} = 8mA I _{G1} to I _{G4} = 0

Typical Application Circuit

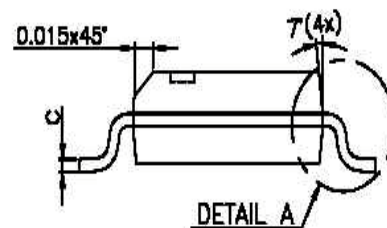
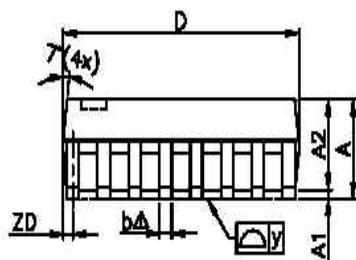
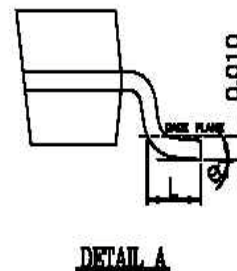
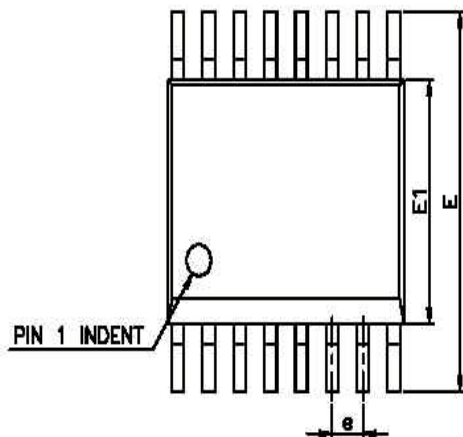


Typical Characteristics





Package Outlines : 16-pin SSOP



SYMBOL	MILLIMETERS			INCHES		
	MIN	TYP	MAX	MIN	TYP	MAX
A	1.35	1.60	1.75	0.053	0.063	0.069
A1	0.10	0.15	0.25	0.004	0.006	0.010
A2	-	-	1.50	-	-	0.059
b	0.20	-	0.30	0.008	-	0.012
C	0.18	-	0.25	0.007	-	0.010
D	4.80	4.85	5.00	0.189	0.191	0.197
ZD	-	0.20	-	-	0.008	-
E	5.79	5.99	6.20	0.228	0.236	0.244
E1	3.81	3.91	3.99	0.150	0.154	0.157
L	0.41	0.71	1.27	0.016	0.028	0.050
e	-	0.64	-	-	0.025	-
y	-	-	0.076	-	-	0.003
θ	0°	-	8°	0°	-	8°